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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
. 09/764,242	01/19/2001	George Wong	CS98-070B	8930	
28112	7590 03/05/2003			·	
GEORGE O.	SAILE & ASSOCIATE	EXAMI	EXAMINER		
28 DAVIS AV POUGHKEEP			DIAZ, JOSE R		
			ART UNIT	PAPER NUMBER	
			2815		
	,		DATE MAILED: 03/05/2003	DATE MAILED: 03/05/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
Advisory Action	09/764,242	WONG, GEORGE	
<b>,</b>	Examiner	Art Unit	
	José R Díaz	2815	
The MAILING DATE of this communication appe	ears on the cover sheet with th	correspondence addr	ess
THE REPLY FILED 10 February 2003 FAILS TO PLACE Therefore, further action by the applicant is required to a final rejection under 37 CFR 1.113 may only be either: (1 condition for allowance; (2) a timely filed Notice of Appea Examination (RCE) in compliance with 37 CFR 1.114.	void abandonment of this applic ) a timely filed amendment whic	ation. A proper reply th places the applicat	to a tion in
PERIOD FOR RE	EPLY [check either a) or b)]		
a) The period for reply expiresmonths from the mailing b) The period for reply expires on: (1) the mailing date of this a no event, however, will the statutory period for reply expire ONLY CHECK THIS BOX WHEN THE FIRST REPLY WAS 706.07(f).  Extensions of time may be obtained under 37 CFR 1.136(a). The fee have been filed is the date for purposes of determining the period of	Advisory Action, or (2) the date set forth later than SIX MONTHS from the mailing FILED WITHIN TWO MONTHS OF THE date on which the petition under 37 CF	ng date of the final rejection HE FINAL REJECTION. F FR 1.136(a) and the appro	on. See MPEP opriate extension
fee under 37 CFR 1.17(a) is calculated from: (1) the expiration date of (2) as set forth in (b) above, if checked. Any reply received by the Offi timely filed, may reduce any earned patent term adjustment. See 37 (	the shortened statutory period for reply ice later than three months after the ma	originally set in the final C	Office action; or
1. A Notice of Appeal was filed on Appellant's 37 CFR 1.192(a), or any extension thereof (37 CF			
2. $\square$ The proposed amendment(s) will not be entered be	ecause:		
(a) \( \square\) they raise new issues that would require further	er consideration and/or search (	(see NOTE below);	
(b) They raise the issue of new matter (see Note by	pelow);		
<ul><li>(c)  they are not deemed to place the application i issues for appeal; and/or</li></ul>	in better form for appeal by mate	erially reducing or sim	nplifying the
(d) they present additional claims without cancel NOTE:	ing a corresponding number of	finally rejected claims	<b>;</b> .
3. Applicant's reply has overcome the following reject	ion(s):		
4. Newly proposed or amended claim(s) would canceling the non-allowable claim(s).	l be allowable if submitted in a s	eparate, timely filed a	amendment
5. ☑ The a) ☐ affidavit, b) ☐ exhibit, or c) ☒ request for application in condition for allowance because: See		idered but does NOT	place the
6. The affidavit or exhibit will NOT be considered bed raised by the Examiner in the final rejection.	cause it is not directed SOLELY	to issues which were	newly
7. For purposes of Appeal, the proposed amendment explanation of how the new or amended claims w			nd an
The status of the claim(s) is (or will be) as follows:			
Claim(s) allowed:			
Claim(s) objected to:			
Claim(s) rejected: <u>18-22</u> .			
Claim(s) withdrawn from consideration:	/	·	
8. The proposed drawing correction filed on is	1	proved by the Examir	ier.
9. Note the attached Information Disclosure Stateme	ent(s)( PTO-1449) Paper No(s)	1 ×	
10. Other:		EDDIE LEE	40 420 FD
		JISORY PATENT <b>EXAM</b> HNOLOGY CENTER <b>28</b> 0	

Continuation of 5. does NOT place the application in condition for allowance because: the reference Saitou et al. anticipates the claimed invention. In summary, Applicant argues that Saitou et al. fails to teach a patterned fill layer, a planar silicon oxide layer, and a multilevel metal structure. However, the Examiner disagrees. With regards to the patterned fill layer, the reference Saitou et al. teaches a patterned conductive layer formed in the semiconductor region (2) and in the kerf areas (3) (see Figure 2). Please note, that the patterned conductive layer formed in the kerf areas is identified by the reference sign (6) (see Figure 1), both formed of the same metal material (please note that regions 6 and 10 are shown in Figure 2 having the same line pattern). In addition, the reference Saitou et al. teaches that the kerf area (3) are filled with the conductive layer (8) (see Figure 1) and the patterned conductive layer (6) (see Figure 2). Please note that Figure 1 does not show the patterned conductive layer (6) because the patterned conductive layer (6) is formed under the conductive layer (8) (see Figure 2). Thus, the patterned conductive layer (6) of Saitou et al. is a "patterned fill layer" since the patterned conductor region.

With regards to the planar silicon oxide layer, the Examiner disagrees with Applicant. Saitou et al. teaches a silicon oxide layer (7) formed on the patterned fill layer (6) (see Figure 2). After a carefully review of the drawings, the Examiner concluded that Figure 3, which is a cross sectional view of Figure 1, further provides the teaching of a planar layer, as required by Applicant. Figure 3 shows that, the silicon oxide layer (7) is planar over the surface of the patterned fill layer (6). Consequently, the reference Saitou et al. anticipates the claimed limitation since Saitou et al. teach a planar silicon oxide layer formed over the patterned fill layer.

Finally, with regards to the multilevel metal structure, the Examiner would like to point out that the reference Saitou et al. clearly anticipates such a limitation in column 6, lines 61-65, wherein Saitou et al. states that multilevel metal structure can also be formed as required. Therefore, Saitou et al. anticipates the claimed limitation of providing a multilevel metal structure.